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Hardware System Verification (HSV) Vertical Solutions Engineering (VSE)

LPDDR2
Palladium Memory Model
User Guide

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General Information

The Cadence Memory Model Portfolio provides memory device models for the Cadence Palladium XP, Palladium XP II and Palladium Z1 series systems. Optimizing the acceleration and/or emulation flow on these platforms for MMP memory models may require information outside the scope of the MMP user guides and related MMP documentation.

1.1 Related Publications

For basic information regarding emulation and acceleration, please refer to the following documents:

For Palladium XP and Palladium XP II:

UXE User Guide
UXE Library Developer's Guide
UXE Known Problems and Solutions
UXE Command Reference Manual
Palladium XP Planning and Installation Guide
Palladium Target System Developer's Guide
What's New in UXE

For Palladium Z1:

VXE User Guide
VXE Library Developer's Guide
VXE Known Problems and Solutions
VXE Command Reference Manual
Palladium Z1 Planning and Installation Guide
Palladium Target System Developer's Guide
What's New in VXE

LPDDR2 Memory Model

1. Introduction

The Cadence Palladium LPDDR2 Model is based on the JEDEC specification JESD209-2A.

The model only supports the S4 and S2 Types. NVM is not supported.

The model is available in several configurations with model sizes to match real devices manufactured by the following vendors: Micron and Samsung.

Currently only a few different sizes are available, please consult the memory model catalog for the current available list.

2. Model Release Levels

All models in the Memory Model Portfolio are graded with a release level. This release level informs users of the current maturity and status of the model. All families in the library are graded at one of these levels.

The different levels give an overall indication of the amount of testing, level of quality and feature availability in the model. For details on supported features check the User Guide for that particular model family.

There are three release levels for models in the MMP release.

Release Level		Model Status	Available in Release	Listed in Catalog	Requires Beta Agreement
Mainstream Release	MR	Fully released and available in the catalog for all customers to use.	Yes	Yes	No
Emerging Release	ER	Model has successfully completed Beta engagement(s). Most, but not all features have been tested. Documentation is available.	No	Yes	Yes
Initial Release	IR	Model has completed initial development and has been released to Beta customer(s). The model may have missing features, may not be fully tested, may not have documentation. Model may contain defects.	No	Yes	Yes

Access to Initial and Emerging Release versions of the models will require a Beta Agreement to be signed before the model can be delivered.

3. Features

The LPDDR2 Palladium memory model is based on the JEDEC specification JESD209-2A. Below table lists which features are supported and which are unsupported. Please refer to the *JESD209-2A* for detailed information.

Table 1: Features List of LPDDR2 Model

FEATURE	SUPPORT	NOTE
Initialization sequence	Yes	
Activate command	Yes	
Burst Read operation	Yes	
Burst Write operation	Yes	
Write Data Mask	Yes	
Precharge/auto-precharge operation	Yes	
Refresh/self-refresh command	Yes	
BST command	Yes	
Partial Array Self-Refresh (PASR)	No	
Mode Register Read command	Yes	
Mode Register Write command	Yes	
DQ Calibration	No	
ZQ Calibration	Partial	Only support value of 0xFF, Calibration command after initialization
NVM function	No	

4. Configurations

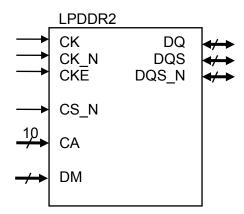
The following table lists the possible configurations. Not all configurations are available from all vendors. Please consult the appropriate vendor site for details on the parts they offer.

Table 2: Model Configurations

		64Mb	128Mb	256Mb	512Mb	10	Gb	20	G b	4Gb	8Gb
Data Width	Type	S2/S4	S2/S4	S2/S4	S2/S4	S2	S4	S2	S4	S2/S4	S2/S4
	Banks	4	4	4	4	4	8	4	8	8	8
νο.	Row Address	A[11:0]	A[11:0]	A[12:0]	A[12:0]	A[13:0]	A[12:0]	A[14:0]	A[13:0]	A[13:0]	A[14:0]
х8	Column Address	A[8:0]	A[9:0]	A[9:0]	A[10:0]	A[10:0]	A[10:0]	A[10:0]	A[10:0]	A[11:0]	A[11:0]
v16	Row Address	A[11:0]	A[11:0]	A[12:0]	A[12:0]	A[13:0]	A[12:0]	A[14:0]	A[13:0]	A[13:0]	A[14:0]
x16	Column Address	A[7:0]	A[8:0]	A[8:0]	A[9:0]	A[9:0]	A[9:0]	A[9:0]	A[9:0]	A[10:0]	A[10:0]
x32	Row Address	A[11:0]	A[11:0]	A[12:0]	A[12:0]	A[13:0]	A[12:0]	A[14:0]	A[13:0]	A[13:0]	A[14:0]
X32	Column Address	A[6:0]	A[7:0]	A[7:0]	A[8:0]	A[8:0]	A[8:0]	A[8:0]	A[8:0]	A[9:0]	A[9:0]

5. Model Block Diagram

The widths of the CA, DM, DQ, DQS and DQS_N buses are dependent on the density of the part being used.



6. Model Parameter Descriptions

The following table provides details on the user adjustable parameters for the Palladium LPDDR2 Memory Model. These parameters may be modified when instantiating an LPDDR2 wrapper or, if necessary, by modifying the HDL parameter declarations and default values which are exposed for access and debug visibility.

Table 3: User Adjustable Parameters

User Adjustable Parameter	Default Value	Description
data_bits	32	Data bus width
addr_bits	10	CA bus width
bank_addr_width	3	Bank address width
row_addr_width	14	Row address width
col_addr_width	10	Column address width
tDQSCK	1	Timing parameter tDQSCK

The following table provides some information about exposed localparams that are NOT user adjustable. On rare occasion the user may find one of these localparam needs adjusting for their configuration. If this case arises, please contact Cadence emulation or MMP support.

Table 4: Visible Non-User-Adjustable Localparam

Localparam	Default Value	Description
byte_width	8	Byte bits
mode_reg_width	8	Mode register address width
num_bytes	4	Data width in bytes

total_addr_bits	bank_addr_width+row_addr_width	Memory capacity address
	+col_addr_width	width
banks	1< <bank_addr_width< td=""><td>Number of banks</td></bank_addr_width<>	Number of banks
mem_depth	64'b1 << total addr bits	memory core depth

Note that there are additional exposed localparams in the model hdl that are not described here nor intended to be described here. These additional localparams are exposed for debugging purposes only and will not be described herein.

7. Address mapping

The array of the LPDDR2 model is mapped into the internal memory of the Palladium system. This array is a single two dimensional array. The mapping of bank, row and column addresses to the internal model array is as follows:

This information is required if the memory needs to be preloaded with user data.

The array name in the model hierarchy is: memcore

If {row,ba,col} addressing is needed instead of the default {ba,row,col} addressing, add +define+MMP_RBC to the vlan invocation (IXCOM flow) or to the appropriate HDL-ICE synthesis (Classical flow) command. No value is required for MMP_RBC – only the compile phase define. This option is applicable when using the <model>.vp file.

8. Register Definitions

In the LPDDR2 specification there are up to 256 registers defined. The LPDDR2 Palladium model implements the following registers.

Register Number	Register Name	Read/Write
0	Device Info	R
1	Device Feature 1	W
2	Device Feature 2	W
3	IO Config 1	W
4	SDRAM Refresh	R
5	Basic Config 1	R
6	Basic Config 2	R
7	Basic Config 3	R
8	Basic Config 4	R
10	IO Calibration	W
16	PASR Bank	W
17	PASR Seg	W
63	Reset	W

8.1. MR0 Device Info Register

The device info register is implemented in the LPDDR2 model. The model supports the following bits.

Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
	N/A						

8.2. MR1 Device Feature 1 Register

Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
nWR		WC	BT		BL		

Bit 7	Bit 6	Bit 5	nWR
0	0	0	Not supported
0	0	1	3
0	1	0	4
0	1	1	5
1	0	0	6
1	0	1	7
1	1	0	8
1	1	1	Not supported

Bit 4	Wrap	
0	No Wrap	Supported
1	Wrap	Supported

Bit 3	Burst Type	
0	Sequential	Supported
1	Interleaved	Supported

Bit 2	Bit 1	Bit 0	Burst Length
0	0	0	Not supported
0	0	1	Not supported
0	1	0	4
0	1	1	8
1	0	0	16
1	0	1	Not supported
1	1	0	Not supported
1	1	1	Not supported

8.3. MR2 Device Feature 2 Register

Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
	N	//A			RL 8		

Bit 3	Bit 2	Bit 1	Bit 0	RL/WL
0	0	0	1	RL=3/WL=1
0	0	1	0	RL=4/WL=2
0	0	1	1	RL=5/WL=2
0	1	0	0	RL=6/WL=3
0	1	0	1	RL=7/WL=4
0	1	1	0	RL=8/WL=4
	All of	Not supported		

8.4. MR3 IO Config Register

Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
	N	/A			D	S	

Writing to this register has no functional affect on the LPDDR2 model.

8.5. MR4 SDRAM Refresh Register

Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0		
	SDRAM Refresh Rate								

The function controlled by this register is not supported in LPDDR2 model. Read this register always returns a value of 0.

8.6. MR5 Basic Config 1 Register

Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	
Manufacturer ID								

See JEDEC specification for list of manufacturer codes. The model currently supports Samsung (0x01) and Micron (0xFF).

8.7. MR6 Basic Config 2 Register

	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Ī				Revisio	n ID 1			

Always returns a value of 0.

8.8. MR7 Basic Config 3 Register

Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0		
	Revision ID 2								

Always returns a value of 0.

8.9. MR8 Basic Config 4 Register

Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
IO W	/idth		Den	sity		Ty	ре

Bit 1	Bit 0	Туре			
0	0	S4 SDRAM			
0	1	S2 SDRAM			
1	0	NVM (Not Supported)			
1	1	Reserved			

Bit 5	Bit 4	Bit 3	Bit 2	Density
0	0	0	0	64Mb
0	0	0	1	128Mb
0	0	1	0	256Mb
0	0	1	1	512Mb
0	1	0	0	1Gb
0	1	0	1	2Gb
0	1	1	0	4Gb
0	1	1	1	8Gb
1	0	0	0	16Gb
1	0	0	1	32Gb
·	All of	Not supported		

Bit 7	Bit 6	IO Width
0	0	X32
0	1	X16
1	0	X8
1	1	Not Used

8.10.MR10 Calibration Register

Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Calibration Code							

The initialization sequence requires a write of 0xFF to this register. All other values have no effect on the model.

8.11.MR16/MR 17 PASR Bank and Seg Registers

These register are implemented in the model but their contents have no effect on the function of the model.

8.12.MR63 Reset Register

This register is implemented in the model where the MRW RESET command (MR63) is an integral part of the initialization sequence. This initialization function is the only function MR63 has in this model. The register content is *don't care*.

9. Commands

The LPDDR2 model accepts the following commands:

- Deselect
- NOP
- Mode Register Write
- Mode Register Read
- Activate
- Precharge
- Precharge All
- Read
- Read with AP
- Write
- Write with AP
- Burst Terminate
- Self Refresh

The following table is from the JEDEC Specification. Table 60 on Page 144.

		SDR Command Pins		DDR CA pins (10)													
con.u.	ND /04	CKE		CKE													CIV
SDRAM Command	NVM Command	CK_t(n-1)	CK_t(n)	CS_N	CA0	CA1	CA2	CA3	CA4	CA5	CA6	CA7	CA8	CA9	CK EDGE		
MRW MRW	н	н	L	L	L	L	L	MAO	MA1	MA2	MA3	MA4	MA5				
MICEY	MICTY	"	"	_	MA6	MA7	OP0	OP1	OP2	OP3	OP4	OP5	OP6	OP7	_		
MRR	MRR	н	н	L	L	L	L	н	MAO	MA1	MA2	MA3	MA4	MA5			
					MA6	MA7					Х				—		
Refresh (per bank) ¹¹	-	н	н	L	L	L	Н	L			>	(<u>_</u>		
(per bank)										Х					₹_		
Refresh	_	н	н	L	L	L	Н	Н			>	(
(all bank)										X					Ŧ		
Enter	Enter	н	L	L	L	L	Н				х						
Self Refresh	Power Down	"						,		X					_		
Activate	Activate	н	н	L	L	н	R8/a15	R9/a16	R10/a17	R11/a18	R12/a19	BA0	BA1	BA2	<u>_f</u>		
(bank)	(row buffer)				R0/a5	R1/a6	R2/a7	R3/a8	R4/a9	R5/a10	R6/a11	R7/a12	R13/a13	R14/a14	Ŧ		
Write	Write (RDB)	н	н	L	Н	L	L	RFU	RFU	C1	C2	BA0	BA1	BA2			
(bank)	(RDB)				AP ^{3,4}	C3	C4	C5	C8	C7	C8	C9	C10	C11	₹_		
Read	Read Read (bank) (RDB)	н	н	L	Н	L	Н	RFU	RFU	C1	C2	BA0	BA1	BA2			
(Dank)					AP ^{3,4}	C3	C4	C5	C6	C7	C8	C9	C10	C11	+_		
Precharge (bank)		н	н	н ь	Н	Н	L	Н	AB/a30	X/a31	X/a32	BA0	BA1	BA2			
(Dalik)	(IVID)				X/a20	X/a21	X/a22	X/a23	X/a24	X/a25	X/a26	X/a27	X/a28	X/a29	<u>+</u>		
BST	BST	н	н	L	н	н	L	L			>	(
										Х					<u>+</u>		
Enter Deep Power Down	Enter Power Down	н	L	L	н	н	L				Х				=		
					н	н	н			Х	х				_		
NOP	NOP	н	н	L						x	^				=		
Maintain	Maintain					н	н	н				X				-	
PD, SREF, DPD (NOP)	Power Down (NOP)	L	L	L						х					7		
										х					4		
NOP	NOP	н	н	н						х					7		
Maintain	Maintain		L H				х										
PD, SREF, DPD (NOP)	Power Down (NOP)	L			L H X						T_						
Enter	Enter Enter		,							х					_ _		
Power Down	Power Down	Н	L H							х					—		
Evit	E-iii									х							
PD, SREF, DPD Power Down	L H	н	н						х					Ę_			
Luly 2010					16										n: 2 (

10. Initialization Sequence

The LPDDR2 model requires that the memory controller follows the initialization sequence as documented in the specification. The sequence basically entails the following steps:

- 1. Wait for CKE to asserted
- 2. Write to Mode Register 63 (MRW Reset Command)
- **3.** Write to Mode Register 10 (ZQ Calibration)

The model requires that these steps are performed in the correct sequence in order to complete initialization. The model will not respond to any others commands unless this sequence is completed.

11. Compile and Emulation

The model is provided as a protected RTL file(s) (*.vp). The file(s) need to be synthesized prior to the back-end Palladium compile. An example of the command for compilation (including synthesis) and run of this model in the IXCOM flow is shown below.

The script below shows two example for Palladium classic ICE synthesis:

```
1)
hdlInputFile jedec_4gb_16.vp
hdlImport -full -2001 -l qtref
hdlOutputFile -add -f verilog jedec_4gb_16.vg
hdlSynthesize -memory -keepVhdlCase -keepRtlSymbol -keepAllFlipFlop
jedec_4gb_16
.....

2)
vavlog jedec_4gb_16.vp

vaelab -keepRtlSymbol -keepAllFlipFlop -outputVlog jedec_4gb_16.vg
jedec_4gb_16
.....
```

NOTE: It is common for Palladium flows to require –keepallFlipFlop since it removes optimizations that are in place by default. For example, without –keepAllFlipFlop, HDL-ICE can remove flops with constant inputs and merge equivalent FF. The picture above is modified a bit when ICE ATB mode (–atb) is used since then a constant input FF is only optimized out when there is no initial value for it or the initial value is the same as the constant input value.

It is also common for Palladium flows to require –keepRtlSymbol. This option enables the HDL Compiler to keep original VHDL RTL symbols, such as ".", whenever possible. In other words, it maps VHDL RTL signal name a.b to the netlist entry, \a.b. Without this modifier, the signal name would otherwise be converted to a b in the netlist.

If the recommended compile script includes the aforementioned options, the user must include them to avoid affecting functionality of the design.

12. SWI Smart Memory Interface

This LPDDR2 core model (lpddr2_pd.vp) supports a fixed, Verilog macro controlled interface, or "hooks", to one of the Smart Memory components in Cadence's Software Integrator (SWI) product. Software Integrator (SWI) is a support library that is part of Cadence's Hybrid Solution--a multi-tool system level solution that runs in a hybrid PXP + IES simulation mode and targets the increasing number of SoC performance conscious projects requiring the booting of commercial operating systems and the running of complex software-driven tests against an accurate model of the SoC prior to tapeout.

For additional details about the SWI product at large please consult the SWI product documentation which includes a user guide. This documentation can be accessed via support.cadence.com and is located on the Product Pages/Product Manuals link where SWI 13.1 is located with other Functional Verification products.

The user of the SWI solution who is integrating this core model to the corresponding SWI Smart Memory component side should define the Verilog macro "MMP_SM" to enable the Smart Memory interface. This will enable the portion of the interface that resides in the MMP model core, thus completing access to the implemented SWI Smart Memory functionality.

Table 5: SWI Smart Memory Verilog Define

`define Macro purpose	Possible `define Values
Set the Smart Memory interface to compile "in" as	MMP_SM
part of the memory model	

The SWI Smart Memory interface includes the signals shown in Table 6: SWI Smart Memory Interface Signals. It is outside the MMP scope to treat the integration of the MMP model into a hybrid solution. For additional details, please consult the SWI documentation and other Hybrid Solution documentation.

Table 6: SWI Smart Memory Interface Signals

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NAME	DECLARATION	DESCRIPTION
sm_raddr	output [(total_addr_bits-1):0] sm_raddr	Smart Memory read address

sm_re	output sm_re	Smart Memory read enable
sm_raddr_en	output sm_raddr_en	Smart Memory read address enable
sm_dout	input [data_bits-1:0] sm_dout	Smart Memory read data
sm_waddr	output [(total_addr_bits-1):0] sm_waddr	Smart Memory write address
sm_we	output sm_we	Smart Memory write enable
sm_waddr_en	output sm_waddr_en	Smart Memory write address enable
sm_din	output [data_bits-1:0] sm_din	Smart Memory write data
sm_bw	output [data_bits-1:0] sm_bw	Smart Memory data mask
verbosity	input [3:0] verbosity	Smart Memory debug info display level
		control

The Smart Memory interface includes a user adjustable parameter that passes user data from wrapper layers that are external to this MMP model into MMP model. The single 64-bit parameter is subdivided by field to accommodate data as shown in Table 7: SWI Smart Memory User Adjustable Parameters below. This parameter defaults to a value of '0' and is managed by the SWI product Smart Memory component. For additional details, please consult the SWI documentation and other Hybrid Solution documentation.

Table 7: SWI Smart Memory User Adjustable Parameters

PARAMETER	DESCRIPTION
parameter [63:0] SMConfigSpecific_UserData	Smart Memory User Data Passing
FIELD	DESCRIPTION
[2:0]	Used for specifying device/channel/subpart
[63:61]	Extension value of total_addr_bits

The Smart Memory interface includes non-user adjustable localparams and parameters as shown in <u>Table 8: SWI Smart Memory Non-User Adjustable</u> Parameters below. Note that a localparam of the same name (total_addr_bits) but of different size is part of the standard MMP core model.

Table 8: SWI Smart Memory Non-User Adjustable Parameters

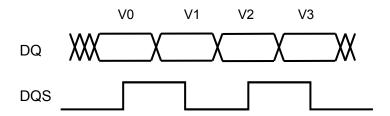
LOCALPARAM	VALUE	DESCRIPTION
total_addr_bits	bank_addr_width+row_addr_width	Memory capacity width
	+col_addr_width +	
	SMConfigSpecific UserData[63:61]	

The SWI Smart Memory interface has dependencies on the inclusion of external file(s). For additional details about purpose and content of any Smart Memory related external files, please consult the SWI documentation and other Hybrid Solution documentation.

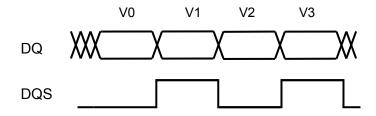
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13. Handling DQS in Palladium Memory Models

For writes to a DDR memory, industry datasheets show each DQS edge centered within the corresponding valid period (v0, v1, v2, etc.) of DQ, as in the following diagram.

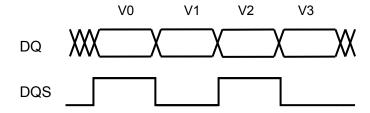


For DDR models provided by Cadence for Palladium, if the design drives DQ and DQS signals with the above timing, the DDR memory will behave correctly. However, to obtain this timing in Palladium, the fastest design clock must toggle twice as frequently as the DQS signal. If this faster clock is not needed for any other reason, the presence of the faster clock will usually cause an unnecessary 2X slowdown in emulation speed. To eliminate the need for a faster clock, you can have the design generate each DQS edge at the end of the corresponding DQ valid period (rather than the middle), as in the following diagram:



Note that the first DQS edge is at the *end* of first valid DQ, not at the beginning.

For reads from the DDR model, the DDR model will drive DQ and DQS with the first DQS edge at the *beginning* of the first valid data, not at the end:



The DDR model behaves this way to conform with industry datasheets for DDR memories. The design reading the data from the DDR model must delay the DQS signal, and use the delayed-DQS signal to sample the DQ. A delay of one Q_FDP0B should work fine, even in CAKE 1X mode. If you are using CAKE 1X mode and the DDR clock is the fastest design clock, the DQ signal will change twice per FCLK, and the Q_FDP0B delaying DQS will provide one-half FCLK delay, so that each delayed-DQS edge is at the end of the corresponding data valid period.

To delay the DQS signal, a commonly used approach is to create a special pad cell for DQS, that has a Q_FDP0B delay cell inserted on the path that leads from the DDR memory into the design.

The user may insert delays into pad cells (or elsewhere in the design) using the below code example which leverages ixc_pulse, an internal primitive that can be used to access FCLK and to create controlled delay, for IXCOM flow and leverages the Q_FDP0B primitive for delay generation in the Classic ICE flow. For more detailed information about ixc_pulse please reference the *UXE User Guide* section called *Generating Pulses*. There is no need for the user to define IXCOM_UXE for the Verilog macro; it is predefined for the user in IXCOM flow. Note that in UXE 13.1.0 and prior the equivalent pulse generating function was named axis_pulse.

```
// Flow independent delay cell
module pxp_fclk_delay (in, out_delay);
input in;
output in;
output out_delay;

reg out_delay;

`ifdef IXCOM_UXE
   wire VCC=1'b1;
   ixc_pulse #(1)(Fclk,VCC);
   always @(posedge Fclk)
      out_delay <= in;
`else
   Q_FDPOB fclk_dly (.D(in), .Q(out_delay));
`endif
endmodule</pre>
```

14. Debugging

This model has several debugging options, techniques and tips that may assist the user may use in isolating a problem.

• For issues that are may not be model specific please review the *Memory Model Portfolio* FAQ for All Models User Guide.

 Golden waveform: A package with a reference waveform is available which shows the following command sequence(s):

(1) Initialization:

CKE is Low

CKE is High and NOP

MRW [Write Mode Register 63, RESET]

MRW [Write Mode Register 10 with 8'hFF, ZQCal Initialization]

Initialization Finished, the signal 'init done' goes high

(2) An additional command sequence includes:

MRW [Write Mode Register 1, Change BL]

MRW [Write Mode Register 2, Change RL/WL]

ACT

WRITE

READ

PRECHARGE

ACT

MASK WRITE

 Debug Display: This MMP memory model has available a built-in debug methodology called MMP Debug Display that is based on the Verilog system task \$display. Please see the *Palladium Memory Model Debug Display User Guide* in the release docs directory for additional information.

Manual Configuring of this MMP Model Family

This MMP model supports manual configuration by accompanying the model mode register or configuration register declarations with synthesis directives, such as keep_net directives, that instruct the compiler to ensure that the relevant nets remain available for runtime forcing. For a general description of this support please see the user guide in the MMP release with path and filename <code>docs/MMP_FAQ_for_All_Models.pdf</code>.

While MMP strongly recommends following protocol-based commands to configure MMP models, MMP recognizes that the design test environment may desire to trade off the risks inherent in streamlining or circumventing the initialization sequence part of the protocol in order to better support some testing environments.

The following table lists the internal register path and naming along with the specification or datasheet naming for model mode registers or configuration registers that are accompanied by keep_net synthesis directives in support of such manual configuration. ONLY writeable configuration registers or fields are supported thusly. Please read the relevant datasheet for details about individual register behavior and mapping to fields.

Table 9: Writeable Mode Register / Configuration Register Info

Hierarchical RTL Naming for Writeable Configuration Related Registers & Signals	Specification or Vendor Datasheet Naming for Configuration Related Registers	Access
<model_name>.MR1_reg</model_name>	MR1	W
<model_name>.MR1_set</model_name>		
<model_name>.MR2_reg</model_name>	MR2	W
<model_name>.MR2_set</model_name>		
<model_name>.MR3_reg</model_name>	MR3	W
<model_name>.MR3_set</model_name>		
<model_name>.MR10_reg</model_name>	MR10	W
<model_name>.MR10_set</model_name>		
<model_name>.MR16_reg</model_name>	MR16	W
<model_name>.MR16_set</model_name>		
<model_name>.MR17_reg</model_name>	MR17	W
<model_name>.MR17_set</model_name>	·	•
<model_name>.init_done</model_name>	[Not Applicable]	1'b1 indicates initialization is complete

Note: The user needs to force the MR#_set to be 1'b1 when forcing MR#_reg.

15. Revision History

The following table shows the revision history for this document

Date	Version	Revision
March 2010	1.0	Initial Release
June 2011	1.1	Added release levels description
Dec 2011	1.2	Added 8Gb configuration
April 2014	1.3	Added section on Configuration Parameters
June 2014	1.4	Added +define+MMP_RBC to select {row,bank,col} addressing.
July 2014	1.5	Add info about MR63 in register definition section. Repair doc properties title.
September 2014	1.6	Remove version from UG file name. Update UXE / IXE documentation reference titles.
September 2014	1.7	Adding Model parameter descriptions section. Added paragraph about flow independent delay cell in "Handling DQS" section.
November 2014	1.8	Remove emulation capacity info. Update related publications list.
July 2015	1.9	Update Cadence naming on front page
September 2015	1.10	Add feature table, compile section and SWI section
January 2016	2.0	Update for Palladium-Z1 and VXE
April 2016	2.1	Update SM interface sm_we
July 2016	2.2	Remove hyphen in Palladium naming
December 2016	2.3	Add "Manual Configuring of DDRx/LPDDRx" section
May 2017	2.4	Update "Manual Configuring of DDRx/LPDDRx" section
August 2017	2.5	Update for new SM interface
October 2017	2.6	Modify "bank" vs "ba" references in Address Mapping section.
January 2018	2.7	Modify header and footer
May 2018	2.8	Add section for Manual configuration
July 2018	2.9	Update for new utility library